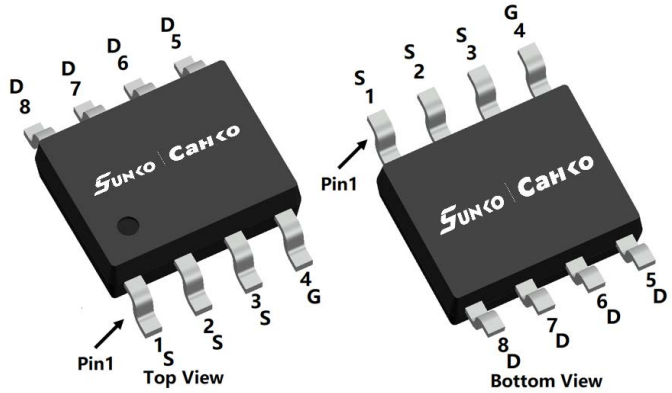
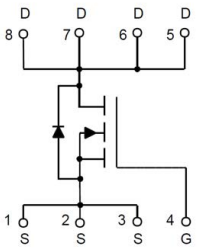
SCS18N03A

N-Channel Enhancement Mode Field Effect Transistor



SOP-8



Product Summary

- V_{DS} 30V
- I_D 18A
- $R_{DS(ON)}$(at V_{GS}= 10V) ＜7.0mohm
- $R_{DS(ON)}$(at V_{GS}= 4.5V) ＜10.0mohm

General Description

- Trench Power LV MOSFET technology
- High density cell design for low $R_{DS(ON)}$
- High Speed switching
- Moisture Sensitivity Level 3
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	30	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	T_A=25℃ @ Steady State	I_D	18	A
	T_A=70℃ @ Steady State		14.5	
Pulsed Drain Current [A]		I_{DM}	65	A
Total Power Dissipation @ T_A=25℃		P_D	3.0	W
Thermal Resistance Junction-to-Ambient @ Steady State [B]		$R_{\theta JA}$	42	℃/ W
Junction and Storage Temperature Range		T_J ,T_{STG}	-55～+150	℃

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
SCS18N03A	F2	Q18N03.	4000	8000	64000	13“ reel

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V			1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±20V, V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	1	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=18A		4.5	7.0	mΩ
		V_{GS}= 4.5V, I_D=10A		6.6	10	
Diode Forward Voltage	V_{SD}	I_S=12A,V_{GS}=0V		0.85	1.2	V
Maximum Body-Diode Continuous Current	I_S				18	A
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=15V,V_{GS}=0V,f=1MHZ		2191		pF
Output Capacitance	C_{oss}			300		
Reverse Transfer Capacitance	C_{rss}			247		
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V,V_{DS}=15V,I_D=20A		46.3		nC
Gate-Source Charge	Q_{gs}			8.8		
Gate-Drain Charge	Q_{gd}			9.2		
Reverse Recovery Chrage	Q_{rr}	I_F=20A, di/dt=100A/us		1.6		
Reverse Recovery Time	t_{rr}			11		ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V, V_{DD}=15V,R_L=0.75Ω R_{GEN}=3Ω		11		
Turn-on Rise Time	t_r			80		
Turn-off Delay Time	$t_{D(off)}$			39		
Turn-off fall Time	t_f			92		

A. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.

B. $R_{\theta JA}$ is the sum of the junction-to-lead and lead-to-ambient thermal resistance, where the lead thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JL}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.

■ Typical Performance Characteristics

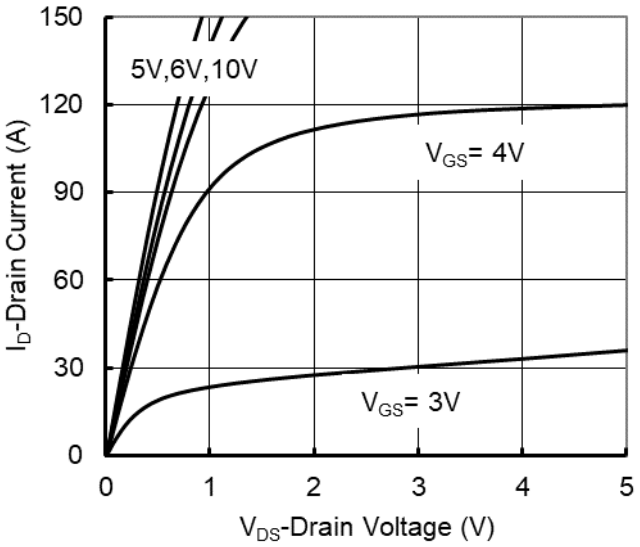


Figure 1. Output Characteristics

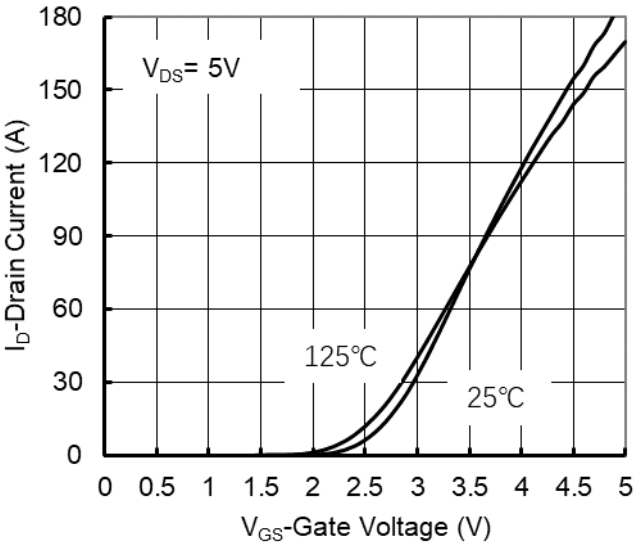


Figure 2. Transfer Characteristics

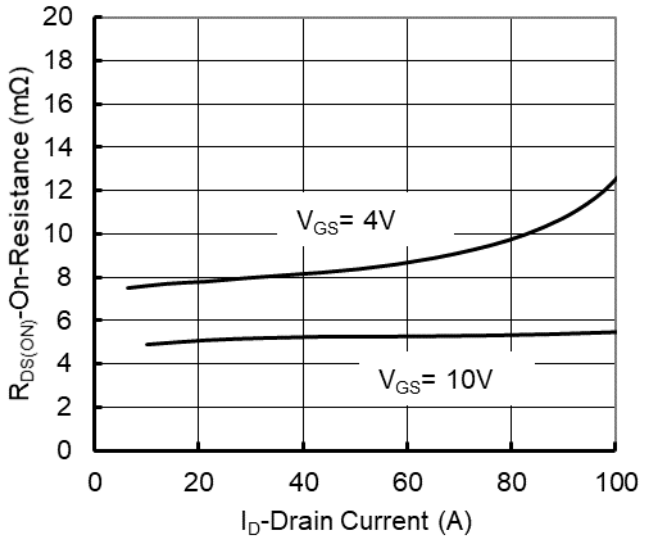


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

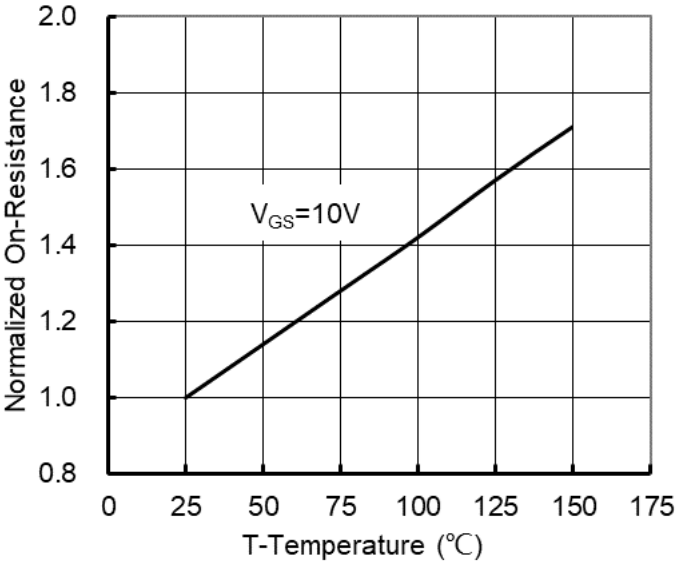


Figure 4. On-Resistance vs. Junction Temperature

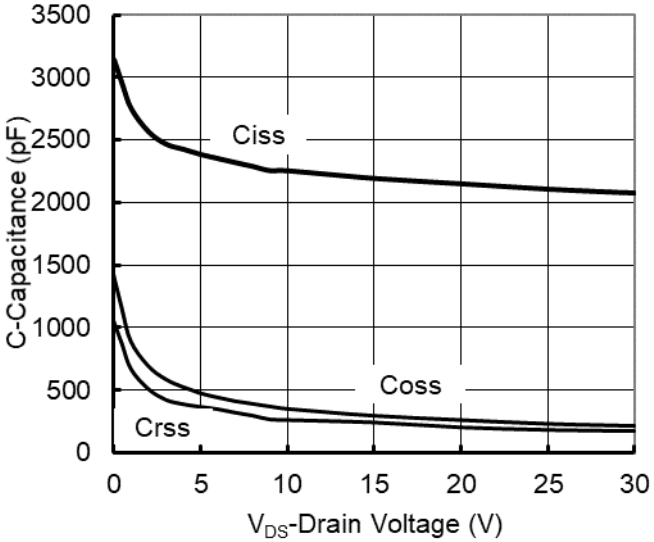


Figure 5. Capacitance Characteristics

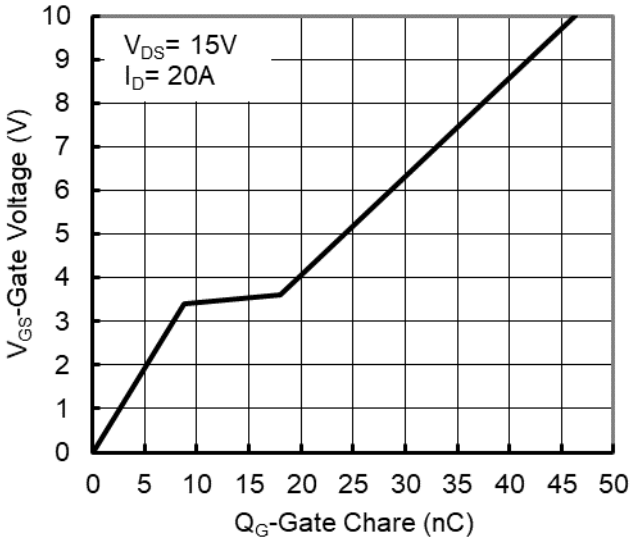


Figure 6. Gate Charge

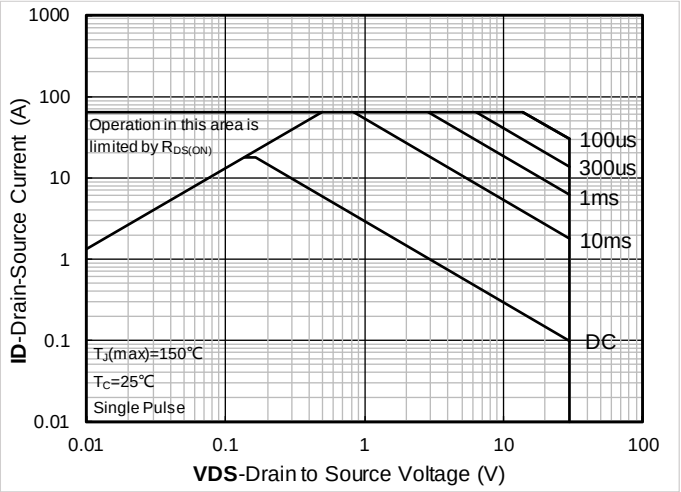


Figure 7. Safe Operation Area

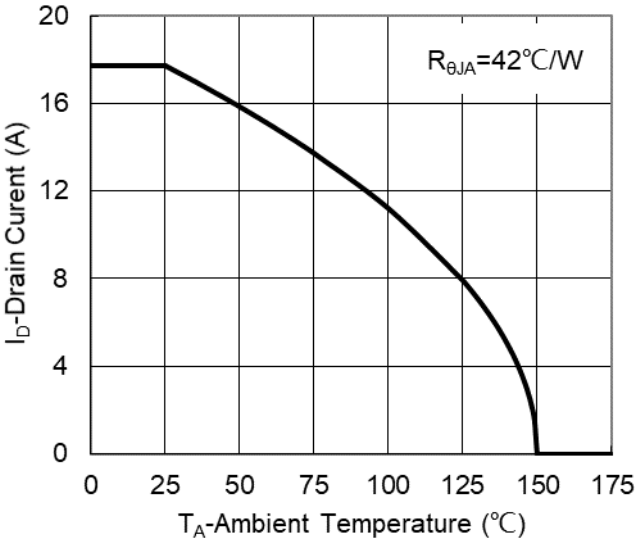


Figure 8. Maximum Continuous Drain Current vs Ambient Temperature

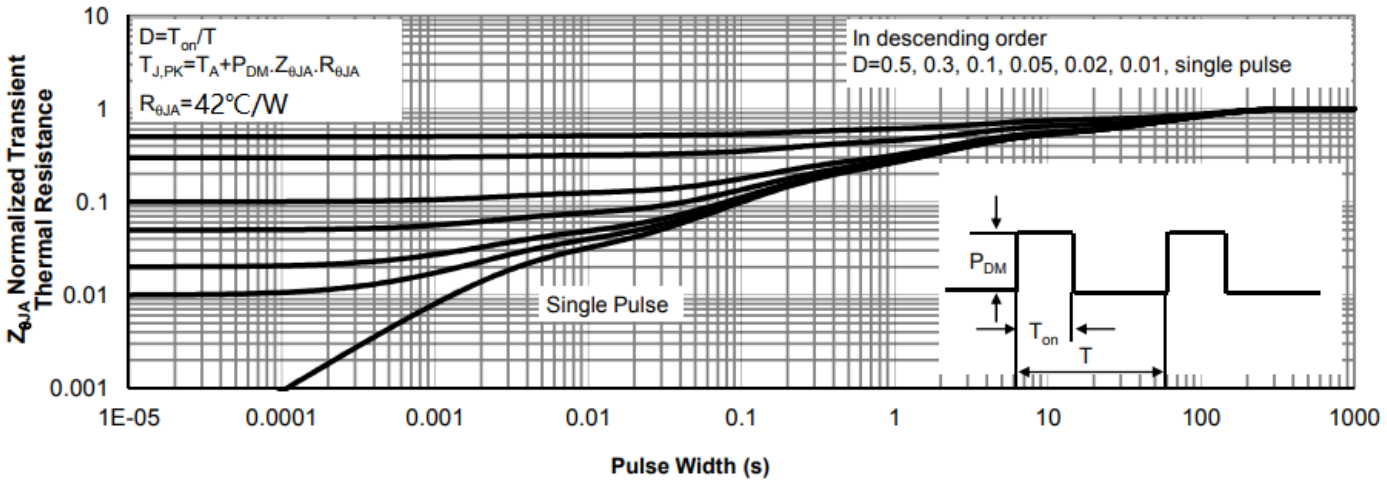
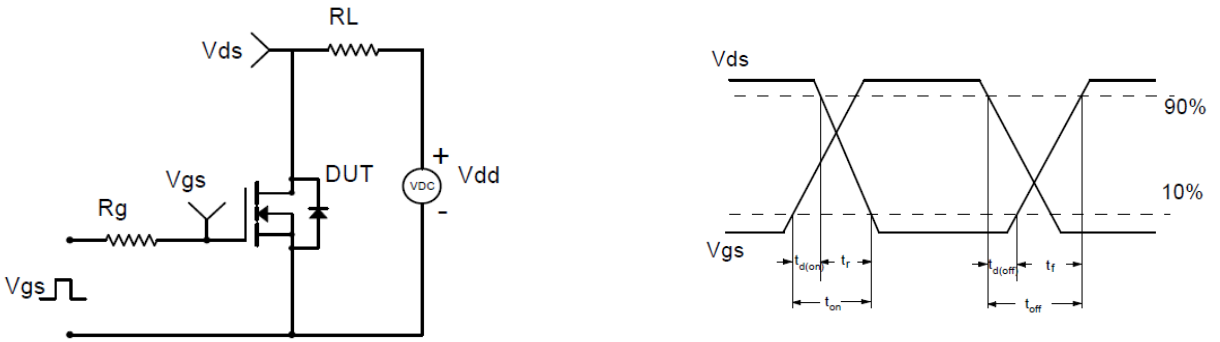
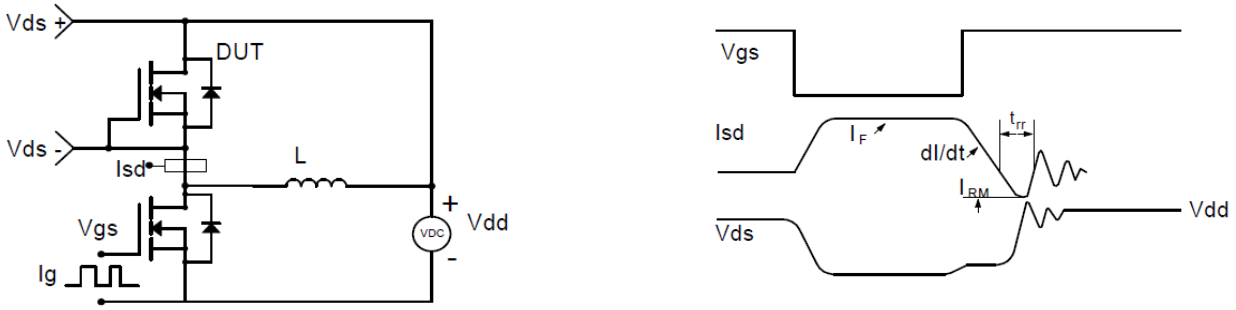


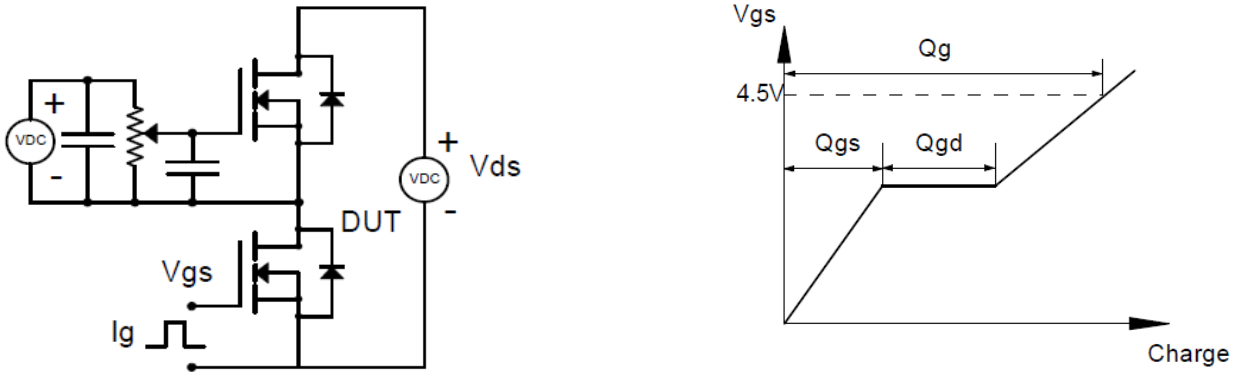
Figure 9. Normalized Maximum Transient Thermal Impedance



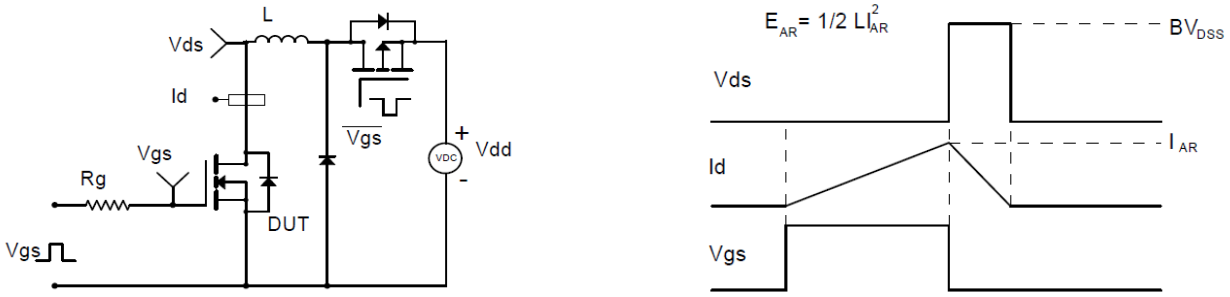
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

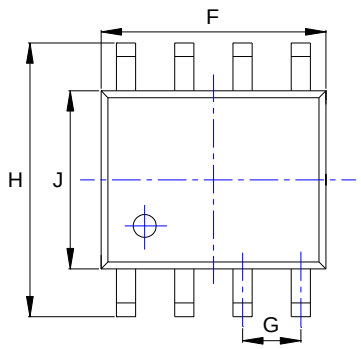


Gate Charge Test Circuit & Waveform

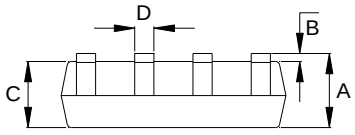


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

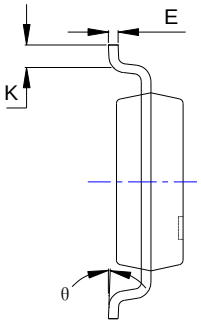
■ SOP-8 Package information



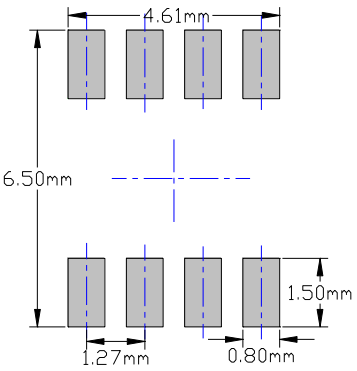
TOP VIEW



SIDE VIEW



SIDE VIEW



Suggested Solder Pad Layout

DIMENSIONS				
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.053	0.069	1.350	1.750
B	0.004	0.010	0.100	0.250
C	0.053	0.061	1.350	1.550
D	0.013	0.020	0.330	0.510
E	0.007	0.010	0.170	0.250
F	0.189	0.197	4.800	5.000
G	0.050BSC		1.270BSC	
H	0.228	0.244	5.800	6.200
J	0.150	0.157	3.800	4.000
K	0.016	0.050	0.400	1.270
θ	0°	8°	0°	8°

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:+/-0.05mm.
3.The pad layout is for reference purposes only.

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